

# Chi-Woo Lee

## List of Publications by Year in descending order

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Version: 2024-02-01

18  
papers

4,648  
citations

567281

15  
h-index

888059

17  
g-index

18  
all docs

18  
docs citations

18  
times ranked

1895  
citing authors

#	ARTICLE	IF	CITATIONS
1	Nanowire transistors without junctions. Nature Nanotechnology, 2010, 5, 225-229.	31.5	1,993
2	Junctionless multigate field-effect transistor. Applied Physics Letters, 2009, 94, .	3.3	768
3	Performance estimation of junctionless multigate transistors. Solid-State Electronics, 2010, 54, 97-103.	1.4	487
4	High-Temperature Performance of Silicon Junctionless MOSFETs. IEEE Transactions on Electron Devices, 2010, 57, 620-625.	3.0	359
5	Reduced electric field in junctionless transistors. Applied Physics Letters, 2010, 96, 073510.	3.3	269
6	Junctionless Multiple-Gate Transistors for Analog Applications. IEEE Transactions on Electron Devices, 2011, 58, 2511-2519.	3.0	234
7	Low subthreshold slope in junctionless multigate transistors. Applied Physics Letters, 2010, 96, .	3.3	195
8	Device design guidelines for nano-scale MuGFETs. Solid-State Electronics, 2007, 51, 505-510.	1.4	100
9	Low-frequency noise in junctionless multigate transistors. Applied Physics Letters, 2011, 98, .	3.3	52
10	Mobility improvement in nanowire junctionless transistors by uniaxial strain. Applied Physics Letters, 2010, 97, .	3.3	38
11	Sensitivity of trigate MOSFETs to random dopant induced threshold voltage fluctuations. Solid-State Electronics, 2008, 52, 1872-1876.	1.4	32
12	Low-temperature conductance oscillations in junctionless nanowire transistors. Applied Physics Letters, 2010, 97, 172101.	3.3	32
13	Investigation of high-performance sub-50nm junctionless nanowire transistors. Microelectronics Reliability, 2011, 51, 1166-1171.	1.7	32
14	Nanowire zero-capacitor DRAM transistors with and without junctions. , 2010, , .		17
15	Comparison of contact resistance between accumulation-mode and inversion-mode multigate FETs. Solid-State Electronics, 2008, 52, 1815-1820.	1.4	16
16	Drain Breakdown Voltage in MuGFETs: Influence of Physical Parameters. IEEE Transactions on Electron Devices, 2008, 55, 3503-3506.	3.0	16
17	Comparison of different surface orientation in narrow fin MuGFETs. Microelectronic Engineering, 2009, 86, 2381-2384.	2.4	5
18	Analytical model for the high-temperature behaviour of the subthreshold slope in MuGFETs. Microelectronic Engineering, 2009, 86, 2067-2071.	2.4	3